



# 100V 57mΩ Dual N-Ch Power MOSFET

## Features

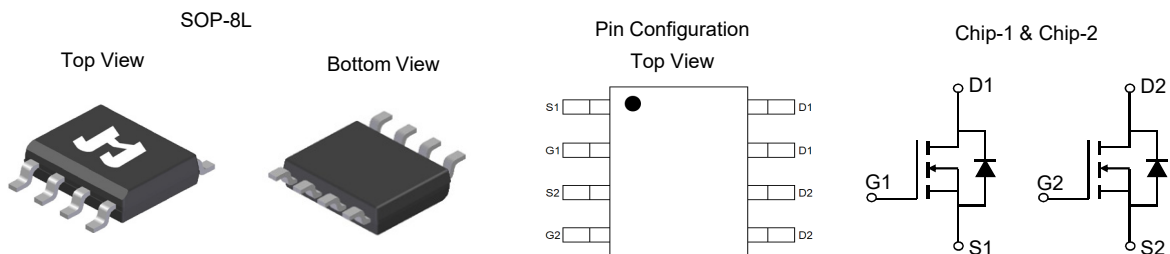
- Low Gate Charge
- 100% UIS Tested, 100% R<sub>g</sub> Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

## Product Summary

Parameter	Value	Unit
V <sub>DS</sub>	100	V
V <sub>GS(th)_Typ</sub>	1.8	V
I <sub>D</sub> (@ V <sub>GS</sub> = 10V) <sup>(1)</sup>	5.5	A
R <sub>DS(ON)_Typ</sub> (@ V <sub>GS</sub> = 10V)	57	mΩ
R <sub>DS(ON)_Typ</sub> (@ V <sub>GS</sub> = 4.5V)	71	mΩ

## Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

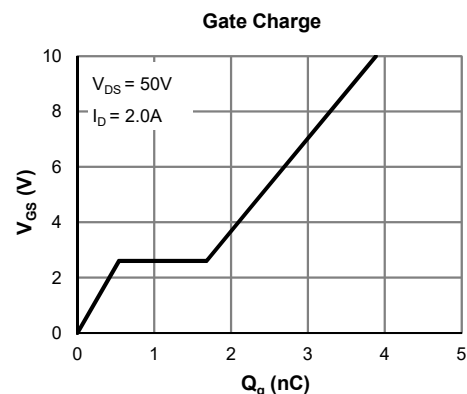
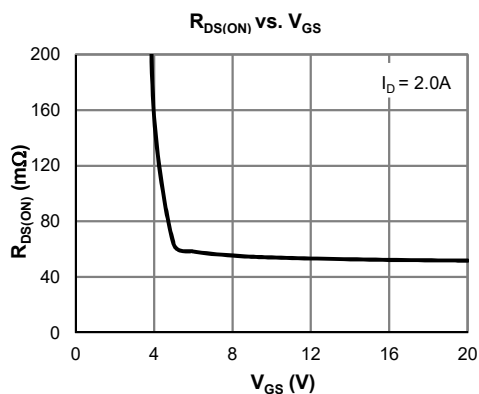


## Ordering Information

Device	Package	# of Pins	Marking	MSL	T <sub>J</sub> (°C)	Media	Quantity (pcs)
JMSL1070APD-13	SOP-8L	8	L1070AD	3	-55 to 150	13-inch Reel	2500

## Absolute Maximum Ratings (@ T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DS</sub>	100	V
Gate-to-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current <sup>(1)</sup>	I <sub>D</sub>	T <sub>C</sub> = 25°C	5.5
		T <sub>C</sub> = 100°C	3.5
Pulsed Drain Current <sup>(2)</sup>	I <sub>DM</sub>	22	A
Avalanche Current <sup>(3)</sup>	I <sub>AS</sub>	4.5	A
Avalanche Energy <sup>(3)</sup>	E <sub>AS</sub>	1.0	mJ
Power Dissipation <sup>(4)</sup>	P <sub>D</sub>	T <sub>C</sub> = 25°C	4.2
		T <sub>C</sub> = 100°C	1.7
Junction & Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C





**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

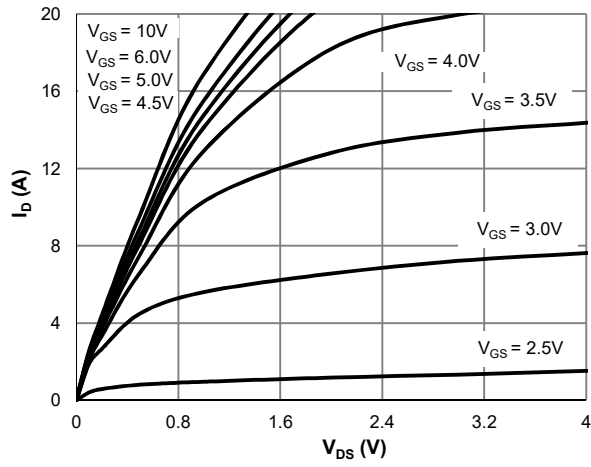
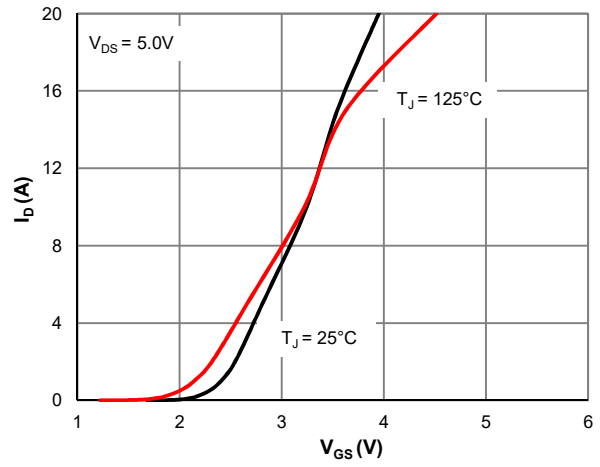
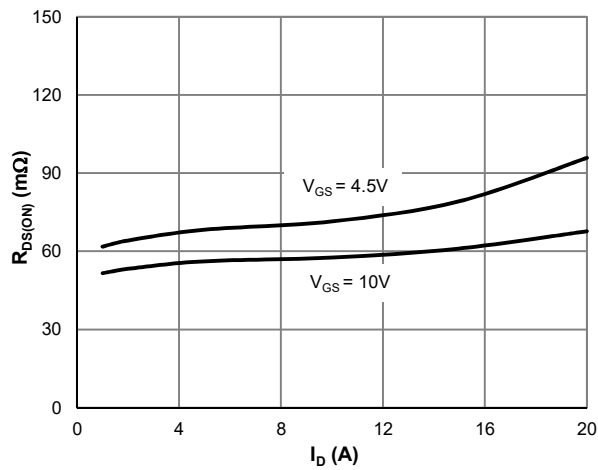
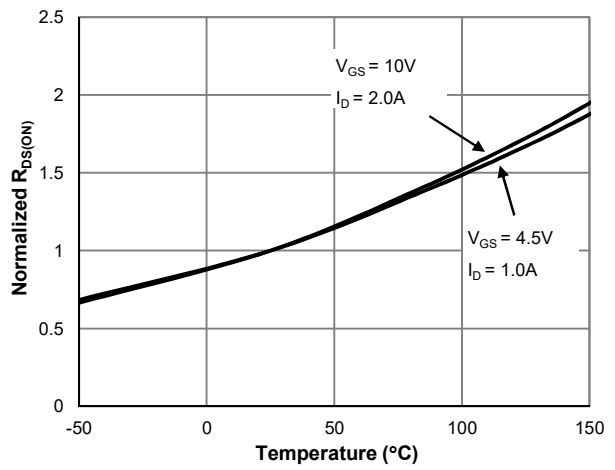
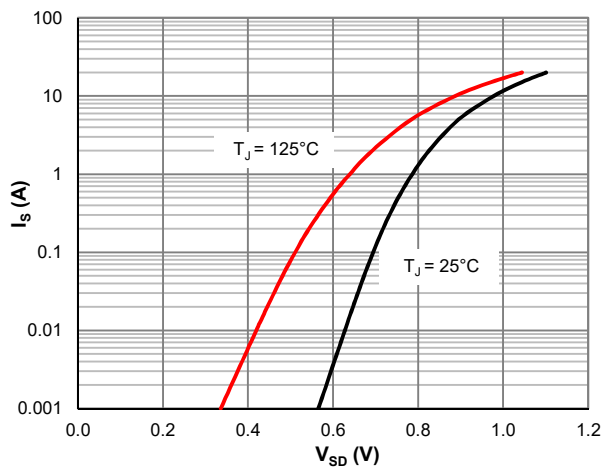
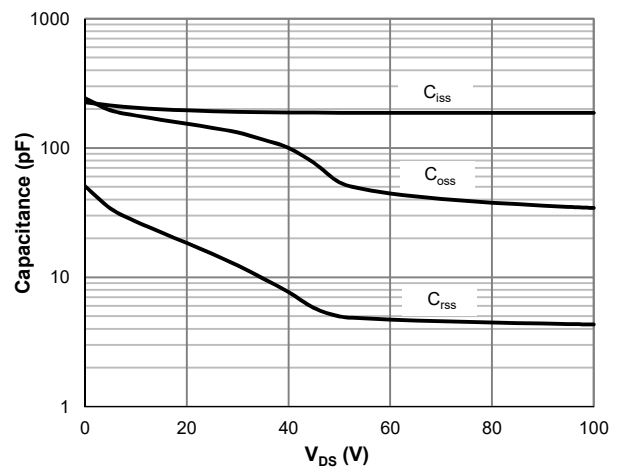
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 2.0\text{A}$		57	70	m $\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 1.0\text{A}$		71	92	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 2.0\text{A}$		11.0		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			4	A
<b>DYNAMIC PARAMETERS <sup>(5)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		187		pF
Output Capacitance	$C_{oss}$			54		pF
Reverse Transfer Capacitance	$C_{rss}$			5.0		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		1.4		$\Omega$
<b>SWITCHING PARAMETERS <sup>(5)</sup></b>						
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 2.0\text{A}$		3.9		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$ )	$Q_g$			2.2		nC
Gate Source Charge	$Q_{gs}$			0.50		nC
Gate Drain Charge	$Q_{gd}$			1.1		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 25\Omega, R_{GEN} = 6\Omega$		2.6		ns
Turn-On Rise Time	$t_r$			3.5		ns
Turn-Off Delay Time	$t_{D(off)}$			9.4		ns
Turn-Off Fall Time	$t_f$			5.5		ns
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 2.0\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		30		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 2.0\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		16.1		nC

**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient ( $t \leq 10\text{s}$ )	$R_{\theta JA}$	30	40	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (steady state)	$R_{\theta JA}$	60	75	$^\circ\text{C}/\text{W}$

**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 150^\circ\text{C}$ .
3. This single-pulse measurement was taken under the following condition [ $L = 100\mu\text{H}, V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ ] while its value is limited by  $T_{J\_Max} = 150^\circ\text{C}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 150^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5: Body-Diode Characteristics**

**Figure 6: Capacitance Characteristics**

Typical Electrical & Thermal Characteristics

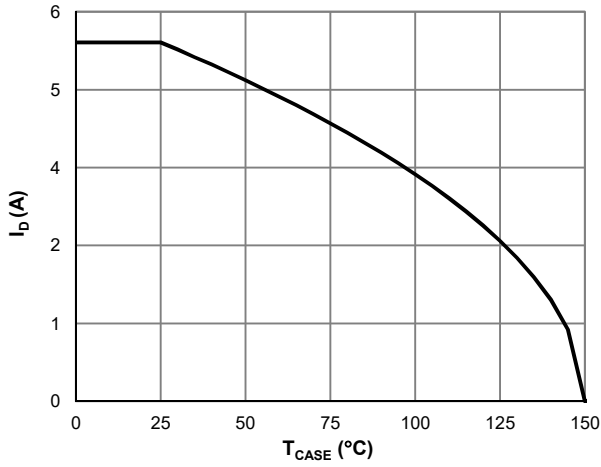


Figure 7: Current De-rating

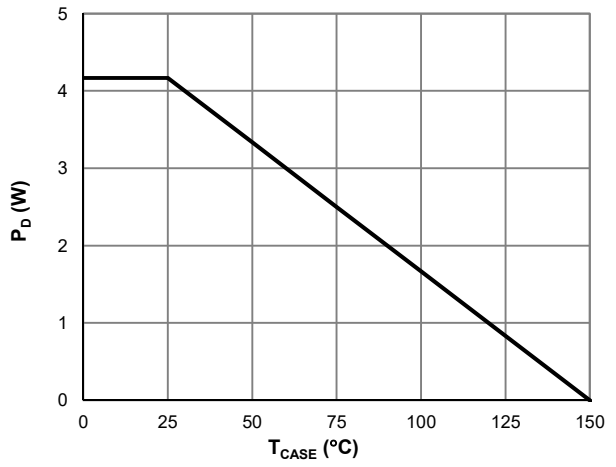


Figure 8: Power De-rating

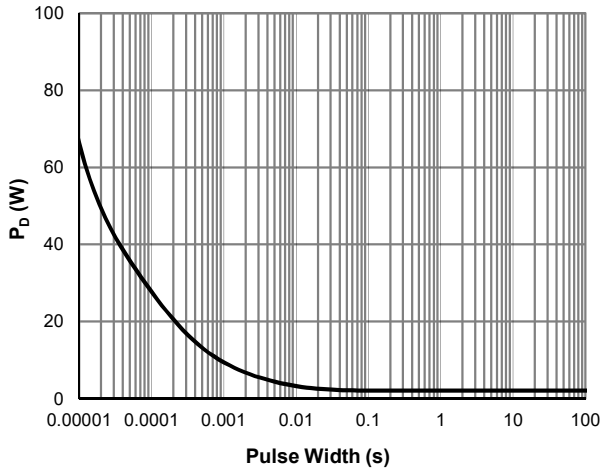
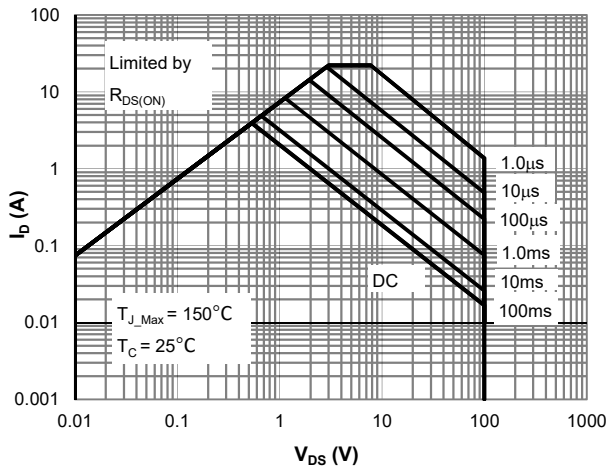


Figure 10: Single Pulse Power Rating, Junction-to-Case

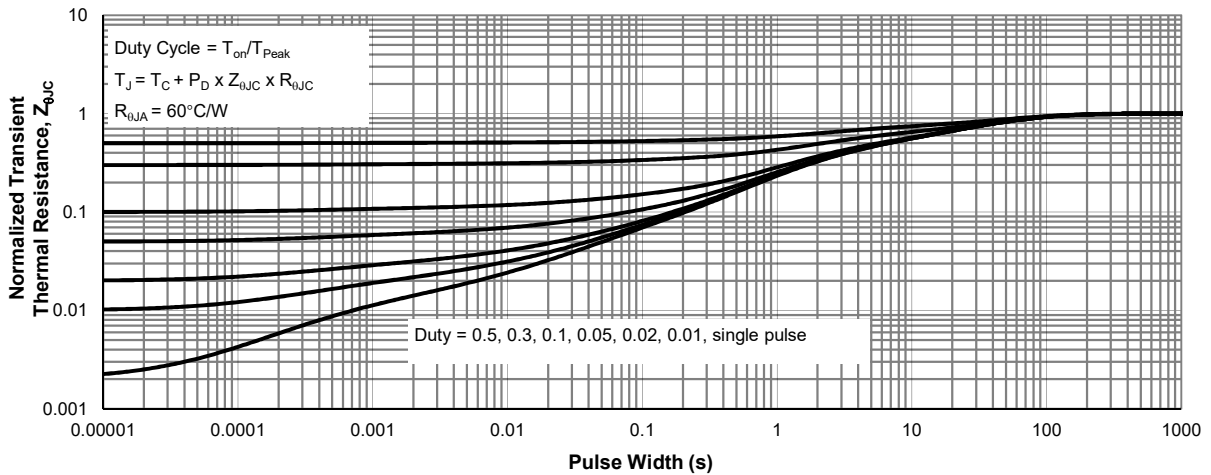
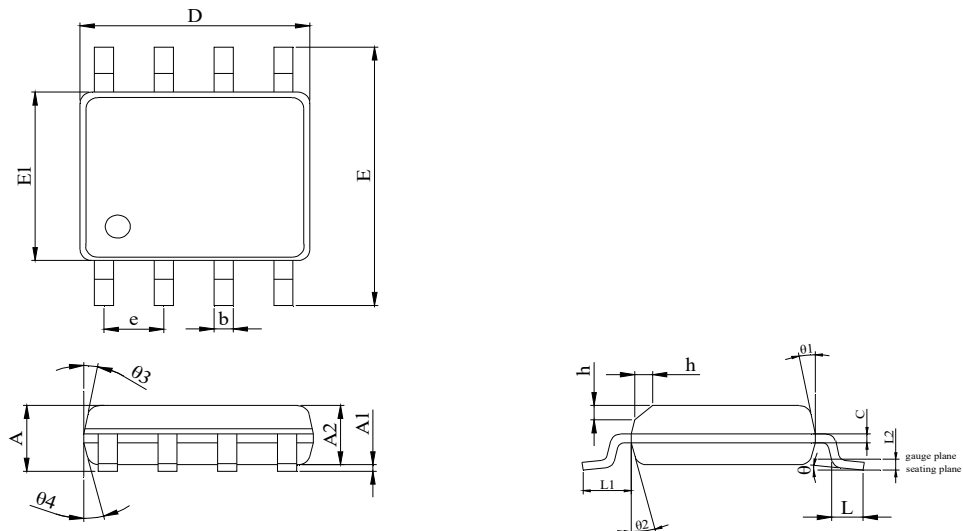


Figure 11: Normalized Maximum Transient Thermal Impedance

**SOP-8L Package Information**
**Package Outline**


DIM	MILLIMETER		
	MIN.	NOM.	MAX.
A	1.35	1.50	1.65
A1	0.05	0.10	0.15
A2	1.35	1.40	1.50
b	0.38	--	0.50
c	0.17	--	0.25
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27(BSC)		
L	0.45	0.60	0.80
L1	1.04 REF		
L2	0.25 BSC		
h	0.30	0.40	0.50
$\theta$	0°	--	8°
$\theta_1$	10°	12°	14°
$\theta_2$	8°	10°	12°
$\theta_3$	10°	12°	14°
$\theta_4$	8°	10°	12°

**Recommend Soldering Footprint**
